Index

A

absorption process, 109–110, 117–118
active gain medium, 106
adiabatic approximation, 44, 325–326
AFM. *See* atomic force microscopy
AIII-BV semiconductors, 243–245
ALD. *See* atomic layer deposition
AlGaAs alloy, 130, 131, 137, 145, 147
arylation, 36, 37f
atomic force microscopy (AFM), 145, 219, 225, 231–247
  contact mode of, 226, 232–233
  DFM. *See* dynamic force microscopy
  optical detection system, 233f
  SFM. *See* scanning force spectroscopy
  tip-surface interaction, 231, 232f
atomic layer deposition (ALD), 206, 214, 215, 219
atomic structure, 53–56, 259f, 260. *See also specific topics*
Aviram-Ratner model, 19–20, 24

B

band-narrowing factor, 331
band-to-band transitions, 110–111, 117
Bardeen-Cooper-Schrieffer (BCS) superfluids, 308
BCS. *See* Bardeen-Cooper-Schrieffer superfluids
Bessel functions, 114, 184
BiCGSTAB (BiConjugate Gradient Stabilised) method, 271
blackbody radiation, 110
Bloch band, 305, 326–327
Bohm theory, 272
Bohr radius, 312
Boltzmann constant, 17, 107
Boltzmann statistics, 276, 284f
Boltzmann temperature relation, 211
Boltzmann transport equation (BTE), 270, 271
Born-Oppenheimer approximation, 44, 325–326
Bose liquid, 308
bottom-up theory, 53–54
Bragg condition, 159
Brillouin zones, 128, 317
Brownian motion, 51
BSIM model, 293
BST materials, 205
BTE. *See* Boltzmann transport equation
bypyridinium ring, 338, 351

C

cadmium selenide (CdSe), 153, 156, 159
CaF_2 crystals, 238, 238f, 243
capacitors, 248f. *See also* dielectrics
Casimir effects, 42
cavities, lasers and, 122–129
CdSe. *See* cadmium selenide
cell phones, 199
charge assignment, 277–280
charge pumping, 83
chemical etching, 8
chemical synthesis, 140–141, 156–157

chemical vapor deposition (CVD), 9, 174, 181
atomic layer method, 9
CIC. *See* cloud-in-cell method
low-pressure, 10
nanocrystal formation, 182
plasma-enhanced, 10
process of, 194
classical physics, 56
cloud-in-cell (CIC) method, 279
complementary MOS (CMOS), 173, 200–204
basic architecture of, 68f
flash memory. *See* flash memory
intrinsic fluctuations in, 260–270, 292
molecular electronics and, 18–31, 257–301
MOSFETs and. *See* MOS field-effect transistors
radiation and, 69
simulation of, 276–301
SPT and, 31–33
computation, theory of, 15–18
condensation, 36
contact-potential difference (CPD), 247
continuous models, 258–259, 259f
corner effects, 98
Coulomb blockade, 174–189, 189
Coulomb interactions, 114, 306, 309, 326–329
Coulomb scattering, 219, 283–284, 290–292
coupling, 78f, 88, 321
CPD. *See* contact-potential difference
crossbar architectures, 22, 24, 25, 25f, 26f, 33, 35f, 42
crystals
Bloch band, 305
defects in, 128
dielectrics and. *See* dielectrics
dimensions of, 127
doping and. *See* doping
energy levels of, 114
nanocrystals. *See* nanocrystals
optical phonons in, 311
polarons in, 305, 315
quantum wires and, 152–153. *See* quantum wires
self-trapping phenomenon, 305
See also specific devices, types
CVD. *See* chemical vapor deposition
cycloaddition, 36, 37f

D

DBR. *See* distributed Bragg reflectors
DD. *See* drift-diffusion method
Debye momentum, 321
decoherence, 44, 44n, 51
demultiplexing, 40
density gradient method, 271–274
deposition, 9–10. *See specific processes*
design gap, 14
DFB. *See* distributed feedback lasers
DFM. *See* dynamic force microscopy
DFT calculations, 215
DG approximation, 281, 284f
DIBL. *See* drain-induced barrier lowering
dielectrics, 200–201, 202t, 204, 208f
atomic-scale variation of, 269f
band gap and, 204, 204f
d-electrons and, 206–213
high-*k* materials, 200–206, 202t, 204f, 213
interface, 219
MOSFETs and., 92–93
new developments, 199–220
polarizability and, 201
trapping and. *See* electron trapping
diffusion, of dopants, 7–8
dimensional effects, 84–94
dimensions, reduction of, 116
discretization method, 263, 276
distributed Bragg reflectors (DBR), 126–127
distributed feedback (DFB) lasers, 159
DIVSB. *See* drain-induced virtual substrate biasing
doping, 7–8, 110, 260–264, 277
drain current, 84, 86f
drain-induced barrier lowering (DIBL), 85, 271
drain-induced virtual substrate biasing (DIVSB), 85
DRAMs. *See* dynamic random access memories, 2
drift-diffusion (DD) method, 263, 271–274

dynamic force microscopy (DFM), 225, 233–234
ac-detection mode, 234
AIII-BV materials, 243–245
block scheme of, 234, 235f
cantilever vibrations, 234–236
chemical sensing with, 244–247
contrast formation, 240
damping signal, 241
embedded nanotip, 240
FM-detection scheme, 234
imaging artifacts, 243
ionic insulator surfaces, 241–243
KPFM technique, 247, 252
snap-to-contact effect, 239
stable performance of, 239
STM and, 243
tip-surface interaction, 236–240, 240–241, 247
dynamic random access memories (DRAMs), 2, 69

E
EDA. *See* electronic design automation
EFTEM. *See* energy-filtered transmission electron microscopy
Ehrenfest theorem, 56
electrical gate oxide thickness (EOT), 199
electrically programmable ROMs (EPROMs), 2, 26
electron trapping, 212f
characteristic time, 209
d-electrons and, 206–213
DC measurements, 208
detrapping, 209, 210f, 213f
dielectrics and, 210f. *See also* dielectrics
fast transient model, 208–209
orbitals of, 201f, 206–213
pulse time and, 213f
quantum effects and, 206–213
shallow, 211, 212
tunneling and, 134
vibrons and, 345
electronic design automation (EDA), 293
electrons
coupling and, 308
energy of, 107–108
phonons and, 309, 311, 326–329, 332
polarons and, 305
Schrödinger equation, 128
semiconductors and, 107
trapping. *See* electron trapping
electrostatic force, 248f
eltran process. *See* epitaxial layer transfer
energy-filtered transmission electron microscopy (EFTEM), 181, 182
EOT. *See* electrical gate oxide thickness
epitaxial growth, 69–70, 137–138
epitaxial layer transfer (eltran), 71–72
EPROMs. *See* electrically programmable ROMs
erase function, 46, 188, 189f, 190f
etching, 8–9, 135, 141
exponential autocorrelation, 266
extraction strategies, 294–296

F
Fabry-Perot cavities, 122, 129
fast transient charging, 208–209
FBEs. *See* floating-body effects
Fermi-Dirac golden rule, 343, 348
Fermi-Dirac statistics, 106, 273, 276, 307
Fermi energy, 229
Fermi levels, 111, 229, 248
fermion operators, 335
FFM. *See* friction force microscopy
FG. *See* floating-gate memory
fiber communication systems, 113–122
field theory, 53
FIPOS. *See* full isolation by porous oxidized silicon
flash memory, 44–52, 45f, 47f, 50f
floating-body effects (FBEs), 78, 87, 90
floating-gate (FG) memory, 171
FN erasure. *See* Fowler-Nordheim erasure
four-gate FET, 99–100
Fourier transforms, 270, 317, 347
Fowler-Nordheim (FN) erasure, 46, 171, 175, 180
friction force microscopy (FFM), 225, 233
Fröhlich constant , 316, 318, 320

Fröhlich polaron,, 308, 317–321, 333, 335
full isolation by porous oxidized silicon (FIPOS), 73

G
GaAs alloys, 139, 155, 244, 246
  cap layer, 150
  heterostructures of, 106
  lasers and, 147. *See also* semiconductor lasers
  quantum wires, 137–139. *See also* quantum wires
  substrate, 149
gain enhancement, 116
Gaussian autocorrelation, 266–267
geometrical magnetoresistance, 90
Giessibl equation, 237
grafting, 27, 42
Green's function, 276, 339–342
Gummel approach, 273
gutterlike potentials, 272

H
Hall effect, 82
Hamaker constant, 239
Hamiltonian function, 335, 345
hardware demultiplexing, 40
harmonic oscillator, 236, 323
Hartree-Fock potential, 311
Heisenberg operator, 341, 347
Heisenberg relation, 15, 51
Hermite polynomials, 323
heterostructures, 106
Hewlett-Packard. *See* HP-UCLA collaboration
HfO_2 films, 204, 215, 218–219, 218f
highly ordered pyrolitic graphite (HOPG), 230
history effects, 78, 91
Holstein model, 321–323, 334
HOMO. *See* highest occupied molecular orbital
HOPG. *See* highly ordered pyrolitic graphite
host-guest technology, 29
hot-carrier injection (HCI), 187
HP-UCLA collaboration, 22–24, 43–44
hydrosilation, 36–39, 37f
hysteresis, 79

I
impact ionization, 79
InAs alloy, 244
information theory, 17
InGaAs layers, 158
InSb surfaces, 244, 245f, 246, 253f
interband transitions, 108, 110–111
International Technology Roadmap for Semiconductors (ITRS), 12, 60, 69, 199, 257
intrinsic parameter fluctuation, 292–301
ion implantation, 7
ionic insulator surfaces, 241–243
ionic switching, 338
irreversibility, 59
ITRS. *See* International Technology Roadmap for Semiconductors

J
Jahn-Teller interactions, 203, 211, 308, 345

K
KBr films, 242f, 249, 253f
Kelvin probe force microscopy (KPFM), 225, 240, 245–253
kink effect, 78
KPFM. *See* Kelvin probe force microscopy
Kronecker symbol, 348

L
λ-ridge quantum wire lasers, 149–150
Lang-Firsov transformation, 329, 333, 334, 346
Langmuir-Blodgett (LB) film, 22
large-scale integration (LSI), 11
lasers
  band-to-band transitions, 117
  nanoscale design, 105–169
  photons and, 117
  semiconductors and. *See* semiconductor lasers
  spontaneous emission, 117

latch, 79
lateral dimension, 135
lateral force microscopy (LFM), 225, 233
lattice polarons, 305–353
LB film. *See* Langmuir-Blodgett film
LDD. *See* low-doped drain
LDOS. *See* local density of states
Lee-Kumpf model, 244
LER. *See* line-edge roughness
LFM. *See* lateral force microscopy
line-edge roughness (LER), 265–268
lithography, 5–7, 40–42, 135–138, 154–157. *See also specific topics*
local density of states (LDOS), 230
Lorentz noise, 91
low-doped drain (LDD), 79
lowest unoccupied molecular orbital (LUMO), 18
LSI. *See* large-scale integration
LUMO. *See* lowest unoccupied molecular orbital

M
macroscopic events, 59
magnetic force microscopy (MFM), 225
masking, 173f
Maxwell demon, 57
Maxwell equations, 128
MBE. *See* molecular-beam epitaxy
mean-field approximation (MFA), 309, 343, 345
measurement problem, 55–59
medium-scale integration (MSI), 11
memory, 24, 171
  array fabrication, 191–195
  characterization of, 191–195
  checkerboard programming, 194, 194f
  CMOS technology and, 192f
  erasure, 46, 188, 189f, 190f
  flash. *See* flash memory
  FN erasure. *See* Fowler-Nordheim erasure
  functional molecules, 60
  nanocrystals and, 192f, 193f
  nonvolatile, 171–196
  NVM, 171–196, 172f
  physics of, 174–181
  process flow for, 192f
  RAM/ROM, 2
  READ operations, 186, 189, 190, 191
  rotaxanes and, 23, 25f
  silicon devices, 171–196
  SRAM cell, 298
  threshold voltage distributions, 193, 193f
  tunneling and, 188
  write, 46
mesh sensitivity, 281–282
mesoscopic level, 27
metal-organic chemical vapor deposition (MOCVD), 130, 131–132, 141
metal-oxide-semiconductor field-effect transistors. *See* MOS field-effect transitors
metastability, 59, 77
MFA. *See* mean-field approximation
MFM. *See* magnetic force microscopy
microdisk cavities, 129
microelectronics, growth of, 12–13, 13f
microprocessors (MPUs), 199
mobility-thickness correlation, 89
MOCVD. *See* metal-organic chemical deposition
molecular-beam epitaxy (MBE), 130–131, 182
molecular electronics, 18–31
  Avogadro number and, 1
  charge conduction, 49
  CMOS, 1–67
  decoherence and, 44n
  dedicated approach, 29, 31–42
  defined, 18
  designed, 18f
  electrical probes, 18
  electrical properties and, 22
  energy structure, 43
  external redox, 20–21
  flash memory. *See* flash memory
  hybrid devices, 27–31, 29f, 59
  internal redox, 19–20
  nanowires. *See* quantum wires
  production costs, 60
  quantum dots. *See* quantum dots
  redox center, 48
  supramolecular systems, 21
  switching and, 338–345, 351

molecular electronics (*cont.*)
wires. *See* quantum wires
See also electrons; *specific devices, topics*
molecular quantum dots (MQDs), 338–348, 340f
Monte Carlo simulators, 271, 283–284
Moore's laws, 257, 351
first law, 2, 3f, 12–15
ITRS and, 12
MOSFET paradigm, 2–5
second law, 3, 4f, 14
MOS field-effect transistors (MOSFETs), 174, 257, 282
atomic-scale variation of, 269f
atomistically doped, 278f
average price of, 3
body potential, 90
boundary conditions and, 274
carrier distributions in, 77
channel thickness, 87–89
classification of, 2
corrections for holes, 283
current technology, 6f
defect coupling, 77
depletion and, 80f
design gap, 14
dielectrics. *See* dielectrics
dimensional effects, 84–94
doping and. *See* doping
double-gate, 88, 94–95
electrical characteristics, 82–83
FBE and, 87–90
Fin Fets, 95
flash devices, 44, 45
front-channel characteristics, 74f
future of, 11
gate-all-around, 98–99
geometrical magnetoresistance, 90
GIFBE in, 90
hole concentration, 284f
length scaling, 85
lithographic limit, 14
logics and, 2
main electrical features, 14
memory. *See* memory
MIGFETs, 95
mobility in, 89
Moore's law and, 2–5
MOSFET paradigm, 10
multiple-gate, 94–100
narrow channels, 86–87
new materials in, 12
p-n junctions, 267
physical limit, 14
potential distribution, 269f
quantum corrections for, 280
quantum simulations for, 98
random dopants, 260–264
Schmitt trigger, 29
self-heating, 92
short-channel effects, 12, 85–86, 93
simulation of, 274, 277, 280, 282–285
SOI basics and, 67–104
source/drain regions, 279
supercoupling, 88
thickness effect, 89
threshold voltage, 74, 174
transconductance, 76, 91
transient time, 80, 84
trapping of holes, 282
triple-gate, 98–99
volume inversion, 76–77, 88
wafer characterization, 81–82
See also specific devices, topics
MPUs. *See* microprocessors
MQDs. *See* molecular quantum dots
MSI. *See* medium-scale integration
multiplexing, 40
multipolaron problem, 309
multispacer patterning, 31, 33–34

N

nanocrystals, 174–181, 176
adatom diffusivity, 184
average charge in, 179
band-gap energy, 114
bitcell characteristics, 185–191
charge loss in, 178
chemical synthesis, 156–157
CMOS and, 257–301. *See* complementary MOS
coalescence of, 183
CVD and, 182
deposition and, 184f, 192
engineering of, 181–185
erase performance, 176

evolution of, 181f
exclusion zone equation, 184
FG memories, 173
growth of, 183
MBE deposition and, 182
memory and, 173, 176, 180, 185–191, 192f, 193f
nucleation and, 183, 183f
optimum size of, 175
passivation, 192
preservation of, 184
quantum dots. *See* quantum dots
self-assembly, 182
self-capacitance of, 174, 175
self-organization, 182, 194
silicon, 171–196
simulation of, 257–301
SONOS devices, 177, 177f, 180
threshold voltage decay, 179
tunneling and, 176, 187
wavefunction inside, 176
wires. *See* quantum wires
See also specific types, topics
nanodevices, defined, 30, 30n
nanometer length scale (NLS), 15, 58
nanostructures, 120, 160, 223–256. *See specific types*
nanotechnology, 223
nanowires, 40–41, 140, 305–353
nanozones, 42
nearest grid point (NGP), 279, 281–282
nearest-neighbor approximation, 332
negative-U Hubbard model, 311, 338–345
Neumann boundary conditions, 274, 275
NGP. *See* nearest grid point
NLS. *See* nanometer length scale
noise factor, 84
nonlinear current-voltage character, 14
nonlinear rate equation, 348
nonvolatile memory (NVM) devices
array fabrication, 191–195
bitcell characteristics, 185–191, 193, 193f
lifetime of, 178
mask adders for, 173f
nanocrystals and, 174–185
NVRAMs, 2, 189–191
TEM image of, 193f
See also specific topics
NOR architecture, 192f
nucleation, 182, 183f
numerical simulations, 260, 309
NVMs. *See* nonvolatile memory

O

observer, role of, 56
optical cavities, 106, 128–129
orbitals structure of, 18, 201f, 206–213, 206–213, 329, 352
oxidation, 7
oxide thickness fluctuations, 268–270
oxide-trimming, 13

P

parasitic bipolar transistor, 79
Pauli principle, 232
Pekar model, 311, 314
perovskites, 200, 336
perturbation theory, 237, 323, 326, 341
phase-lock loop (PLL) device, 234, 235f
phonons, 335, 345–348
photoconductivity, 82
photoluminescence excitation (PLE), 148
photons, 117
emission of, 134
Maxwell equations and, 128
semiconductor lasers and, 117, 122–129
physical etching, 8
physical theory, 53–56
physical vapor deposition (PVD), 9
Planck constant, 16, 110, 230, 271
PLE. *See* photoluminescence excitation
PLL. *See* phase-lock loop
PMMA. *See* polymethyl methacrylate
Poisson equation, 176, 263, 271, 273, 276
Poisson process, 51, 52
Poisson-Schrödinger functions, 276
polarizability, 201, 202, 203
polarons, 321–338
band, 329–331
coupling, 311–321
crystals and, 305
effective mass of, 315–317, 319
electrons and, 305
interaction between, 337f
lattice polarons, 305–353

polarons (*cont.*)
radius of, 315
small, 321, 323–325
switching and, 345–351
wavefunction for, 305
polyacetylene, 338
polycrystals, 213
polymethyl methacrylate (PMMA), 157
polyphenylenevinylene (PPV), 338
PPV. *See* polyphenylenevinylene
prepatterned substrates, 138–140
pseudo-MOS transistor, 81f
PVD. *See* physical vapor deposition

Q
quantum confinement, 115–116, 281
quantum dots, 115
chemical synthesis of, 156, 159
density of states of, 345–348
energy levels, 304f
fabrication technologies, 153–157
Green's function and, 340–342
lithography and, 135, 157
MQDs. *See* molecular quantum dots
self-organization, 154–159
semiconductor lasers and, 157–160
switching and, 305–353
quantum effects
d-electrons and, 201, 203, 206–213
decoherence, 44, 44n, 51
density gradient method, 271
density of states of, 116–117, 129
electron evolution, 52
electron trapping, 206–213
etching and, 135
lateral dimension of, 135
limits posed by, 27, 57
lithography and, 135, 157
measurement problem, 55–56
molecular effects, 42–52
nanostructures and, 115
orbitals, 18, 206–213, 252, 329
polarizability, 201
quantum corrections, 280–281
Zeno effect, 52
See also specific topics
quantum Monte Carlo (QMC) methods, 309, 333
quantum numbers, 115
quantum potentials, 274, 275
quantum well lasers, 115, 121, 129–134, 133f, 154
quantum wires, 40–41
crystalline, 152–153
epitaxial growth and, 137
heterostructures for, 136–137
lithography and, 137, 141–143
nonplanar substrates, 139–140
self-organization and, 137, 143–147, 145
semiconductor lasers and. *See* semiconductor lasers
SILO process, 136
strain-induced lateral ordering, 136–137
switching and, 308–355
T-intersection, 140, 140f, 150–152
V-groove, 138–140, 145, 147–149

R
random access memory (RAM), 2, 23–27. *See also* memory
random doping, 261f, 263, 298, 300
random telegraph signal (RTS), 84
rapid thermal annealing (RTA), 267
rate equation, 340–343, 348–351
read operation, 298–299
real-space representation, 329
recombination processes, 84, 110–111
redox center, 47, 47f, 48
reductionism, 52
resist-ashing, 13
Roadmap. *See* International Technology Roadmap for Semiconductors
rotaxanes, 20–25, 25f, 43
RTA. *See* rapid thermal annealing
RTS. *See* random telegraph signal

S
scanning electron microscopic (SEM), 143, 181
scanning force microscopies (SFM), 223–256, 241
scanning near-field optical microscopy (SNOM), 225

scanning probe microscopy (SPM), 224–227
main components of, 224f
tip for, 224–226
two principal modes of, 227
scanning tunneling microscopy (STM), 225, 228–231
cantilever deflection, 232
tip for, 226f
tip-surface interaction forces, 232
tunneling effect, 228–230
scattering, 219, 290–292, 296
Schmitt trigger, 29
Schrödinger equation, 107, 114, 128, 228, 322, 325
self-heating, 92
self-organization, 27, 136–137, 143–147, 154–159
self-trapping phenomenon, 305
SEM. *See* scanning electron microscopic
semiconductor lasers
band-to-band transitions, 109, 117
basic elements, 106
buried heterostructure, 124
carrier confinement, 125
cavity structures, 122–129
color range, 105–169
confinement and, 125
current status of, 105–160
double-heterojunction, 158, 158f
edge-emitting, 123–125, 125
efficiency of, 121, 124
fiber communication systems, 113–122
four basic types, 122–123
fundamental concepts, 106–111
impact of, 105–169
interband transitions, 108
low threshold, 105–169
miniaturization of, 105–169, 112
modulation bandwidth of, 121
nanoscale design, 113–122
optical cavities, 123–125
optical gain, 105–169
photon confinement, 117, 122–129
quantum cascade lasers, 133–134
quantum dots. *See* quantum dots
quantum well lasers, 121, 130–134, 133f
quantum wire lasers, 134–153
reduced dimensions, 115
room-temperature lasing, 147
self-organized, 136, 143–147, 157–159
spontaneous emission, 117
stimulated emission, 124
surface-emitting, 129
threshold conditions, 118–122
VCSEL model, 125
semiconductor-oxide-nitride-oxide-semiconductors (SONOS) memory, 173–178, 177f, 180
semiconductors
band-to-band transitions, 109f, 117
carrier density, 118
crystalline quality, 112
density of states, 116
doping, 110, 263, 277. *See* doping
electrons in, 106–108
gain function, 116–117
lasers. *See* semiconductor lasers
nanocrystals and, 156. *See* nanocrystals
p-n junctions, 110–112
photons in, 108–110
quantum dots. *See* quantum dots
scaling down in, 199
transistor densities, 199
See also specific types, topics
SFM. *See* scanning force microscopies
Shannon-von Neumann-Landauer theory, 17
Sharfetter-Gummel method, 274
short-channel effects, 85–86, 93
Si/SiO_2 interface, 275–276, 287, 288f, 289f
silanization, 36, 37f
silicates, 205, 214
silicon crystals, 171–195, 172f, 205
silicon-insulator-silicon (SIS) capacitor, 83
silicon lattice basis, 264, 264f
silicon-on-insulator (SOI) technology, 13
basic materials, 70–73, 70f
capacitance and, 83
electrical properties, 81–84
MOSFETs and, 74–81
principles of, 68–70
state-of-the-art technologies, 67
wafer technologies, 70–74
See also specific devices, topics
silicon oxide. *See* SiO_2
SILO. *See* strain-induced lateral ordering process

SIMOX material, 72
SiO_2 layers
  dielectrics and, 192, 199–200, 214–215
  inter facial, 215–217, 217f, 218f, 275–276, 287, 288f
  nanocrystals and, 181–188
  replacement of, 204–205
SIS. *See* silicon-insulator-silicon capacitor
snap-to-contact effect, 232, 239
SNM. *See* static noise margin
SNOM. *See* scanning near-field optical microscopy
SOI. *See* silicon-on-insulator technology
SONOS. *See* semiconductor-oxide-nitride-oxide-semiconductors memory
SOR. *See* successive over-relaxation
SOS. *See* silicon-on-sapphire
SP-STM. *See* spin-polarized scanning tunneling microscopy
spacer patterning technology (SPT), 13, 31–33
spectroscopy, 247
spin-polarized scanning tunneling microscopy (SP-STM), 225
SPM. *See* scanning probe microscopy
spontaneous emission lasers, 117
SPT. *See* spacer patterning technology
sputter-cleaned surfaces, 244
SRAM. *See* static random access memory
$SrTiO_3$ materials, 205
static noise margin (SNM), 297
static random access memory (SRAM), 296–298
statistical compact models, 293
stimulated emission, 117
STM. *See* scanning tunneling microscopy
Stoker model, 182
strain-induced lateral ordering (SILO) process, 136, 143–145
Stranski-Krastanov growth mode, 155
strip-formation stage, 42
successive over-relaxation (SOR), 271
superconductors, 308, 309
supercoupling, 88
switch point voltage, 300
switching, 79, 348–351
  computation and, 22
  current controlled, 352
  nanowires and, 305–353
  polarons and, 338, 345–351
  quantum dots and, 305–353
  reversible, 351, 352
  for simple molecules, 338
Szilard's solution, 57

T

T-intersections, 150–152, 151f
Taurus process, 267, 267f
thermodynamic processes, 206
thin films, 211–215. *See specific types*
threshold current density, 120
threshold voltage, 118–122, 179
TMI. *See* trimethylindium
TOP. *See* trioctylphospine
TOPO. *See* trioctylphosphine oxyde
transconductance, 76, 77, 78f, 91
transient effects, 91
transient time, 79, 84
transistor latch, 79
trimethylindium (TMI), 140
trioctylphosphine oxyde (TOPO), 156
trioctylphospine (TOP), 156
tunneling, 46, 228–230, 229f, 230f, 310, 336, 348

U

UCLA-HP project, 22–24, 43–44
uncertainty principle, 15, 16, 56
unibond, 71, 81f

V

V-groove lasers, 145, 147–149
van der Waals forces, 27, 71, 231, 238, 240
vapor deposition, 9–10. *See specific processes*
vapor-liquid-solid process, 140
variational approach, 311–315
VCO. *See* voltage-controlled oscillator
VCSELs. *See* vertical cavity surface emitting laser
vertical cavity surface emitting laser (VCSELs), 125
vibration wavefunction, 325

voltage-controlled oscillator (VCO), 235
volume inversion, 76–77, 88
von Neumann model, 57

W
wafer technologies, 70–74
Wannier representation, 326–329, 335
wavefunctions, 229, 305. *See* equation XX
Wentzel-Kramers-Brillouin (WKB) approximation, 176, 275
Wigner function, 271
Wilson chamber, 58
wires. *See* quantum wires
write operation, 46, 300

X
X-ray photoemission spectroscopy (XPS), 39

Y
Yablonovitch gap, 127
yttrium-lithium fluoride (YLF) laser, 150

Z
Zeno effect, 52
zeroth mask, 42
ZMR. *See* zone melting recrystallization methods
ZnO nanowires, 152, 152f, 153
zone melting recrystallization (ZMR) methods, 69, 73